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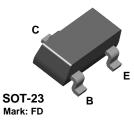
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BCV26



BCV26



PNP Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	10	V
Ic	Collector Current - Continuous	1.2	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCV26	
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/∘C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

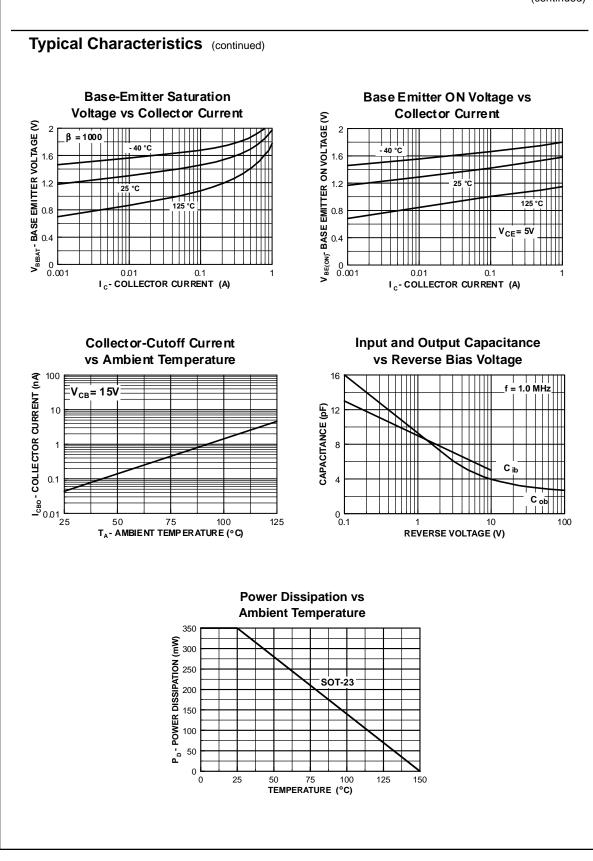
PNP Darlington Transistor (continued)

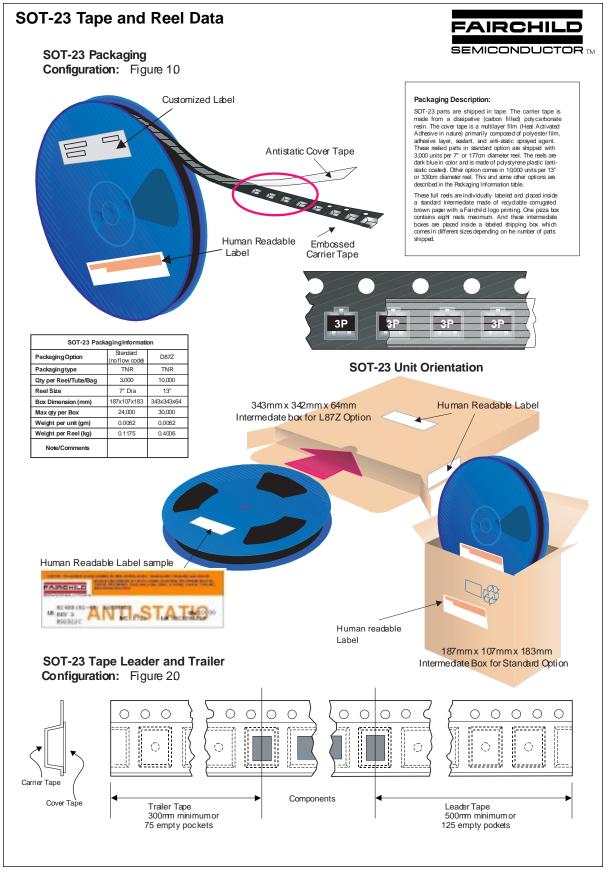
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu \text{A}, I_{\rm E} = 0$	40			v
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \text{ nA}, I_C = 0$	10			V
Сво	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$			0.1	μA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_C = 0$			0.1	μΑ
ON CHAR	ACTERISTICS	I _C = 1.0 mA, V _{CE} = 5.0 V	4,000			
		$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$	10,000			
·	Collector-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$ $I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$	20,000		1.0	V
CE(sat) BE(sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA			1.5	V
()		1				
Т	Current Gain - Bandwidth Product	$I_{C} = 30 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 100 MHz		220		MH:
Cc	Collector Capacitance	$V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$		3.5		pF
	Collector Capacitance ages (V) and currents (A) are negative polarity for PNP	$V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		3.5		pF
		$V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		Satur		pF

PNP Darlington Transistor (continued)

BCV26



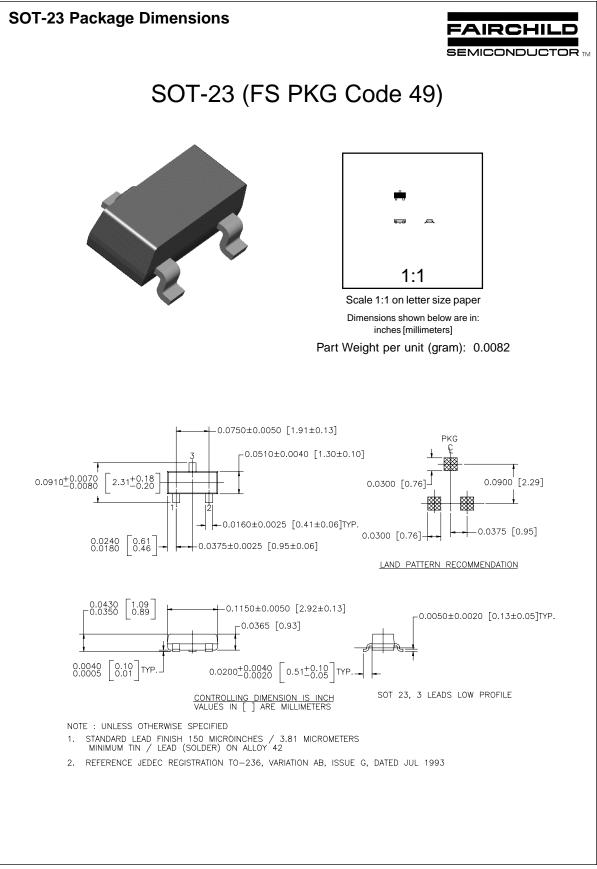


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